74HC123-Q100; 74HCT123-Q100

Dual retriggerable monostable multivibrator with reset

Rev. 1 — 1 August 2012 Product data sheet

1. General description

The 74HC123-Q100; 74HCT123-Q100 are high-speed Si-gate CMOS devices and are pin compatible with Low-power Schottky TTL (LSTTL). They are specified in compliance with JEDEC standard no. 7A.

The 74HC123-Q100; 74HCT123-Q100 are dual retriggerable monostable multivibrators with output pulse width control by three methods:

1. The basic pulse is defined by the selection of the external resistor (R_{EXT}) and capacitor (C_{EXT}).
2. Once triggered, the basic output pulse width may be extended by retriggering the gated active LOW-going edge input ($n\overline{A}$) or the active HIGH-going edge input (nB). By repeating this process, the output pulse period (nQ = HIGH, $n\overline{Q}$ = LOW) can be made as long as desired. Alternatively an output delay can be terminated at any time by a LOW-going edge on input $n\overline{RD}$, which also inhibits the triggering.
3. An internal connection from $n\overline{RD}$ to the input gates makes it possible to trigger the circuit by a HIGH-going signal at input $n\overline{RD}$ as shown in Table 3.

Schmitt trigger action in the $n\overline{A}$ and nB inputs, makes the circuit highly tolerant to slower input rise and fall times.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - Specified from –40 °C to +85 °C and from –40 °C to +125 °C
- DC triggered from active HIGH or active LOW inputs
- Retriggerable for very long pulses up to 100 % duty factor
- Direct reset terminates output pulse
- Schmitt trigger action on all inputs except for the reset input
- ESD protection:
  - MIL-STD-883, method 3015 exceeds 2000 V
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V (C = 200 pf, R = 0 Ω)
- Specified from –40 °C to +85 °C and from –40 °C to +125 °C

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC123D-Q100	−40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HCT123D-Q100				
74HC123PW-Q100	−40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1
74HCT123PW-Q100				
74HC123BQ-Q100	−40 °C to +125 °C	DHVQFN16	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 × 3.5 × 0.85 mm	SOT763-1

4. Functional diagram

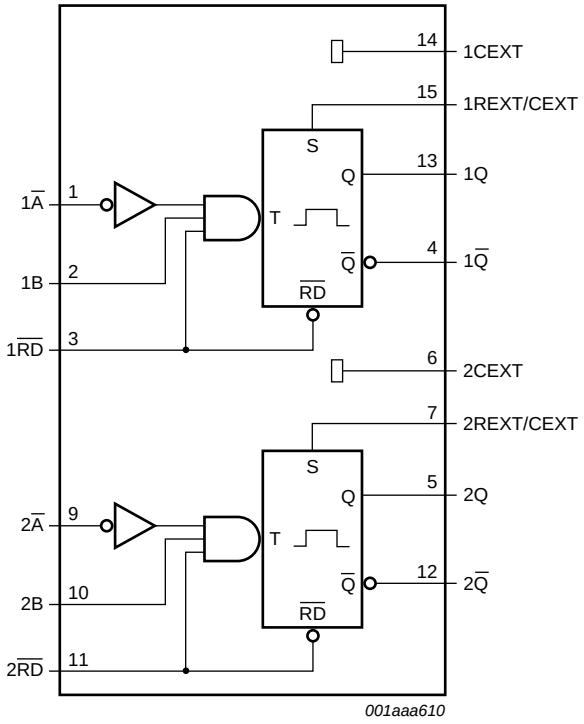


Fig 1. Functional diagram

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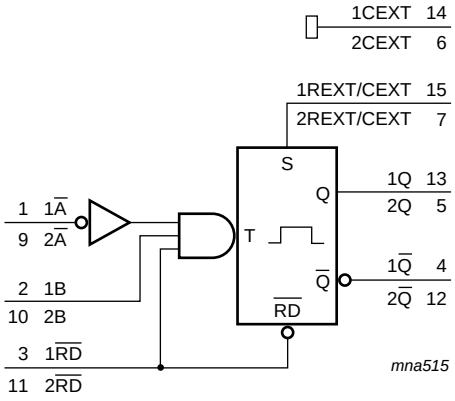


Fig 2. Logic symbol

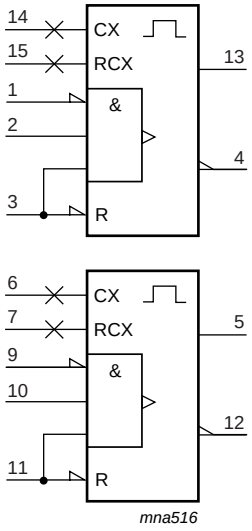


Fig 3. IEC logic symbol

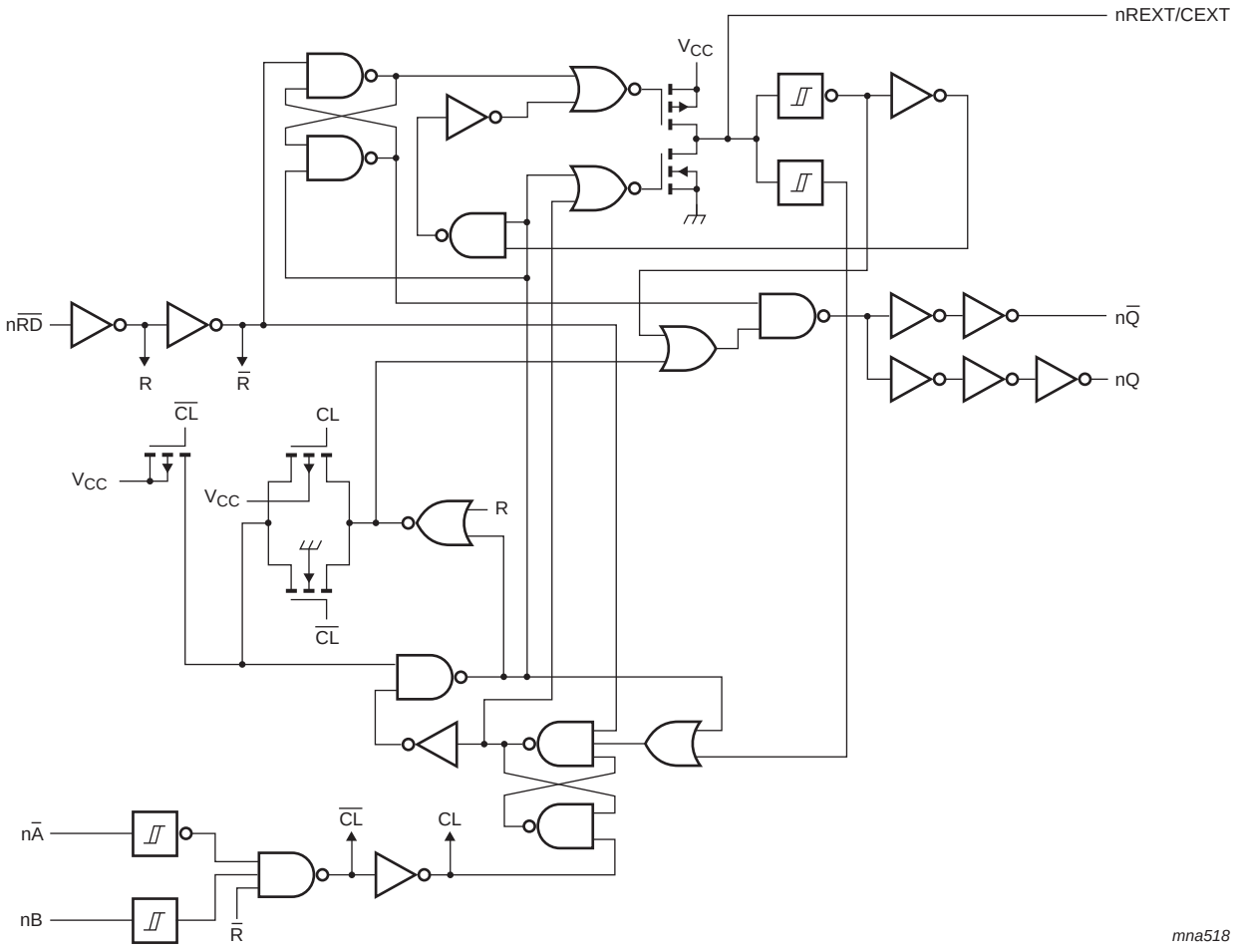


Fig 4. Logic diagram

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5. Pinning information

5.1 Pinning

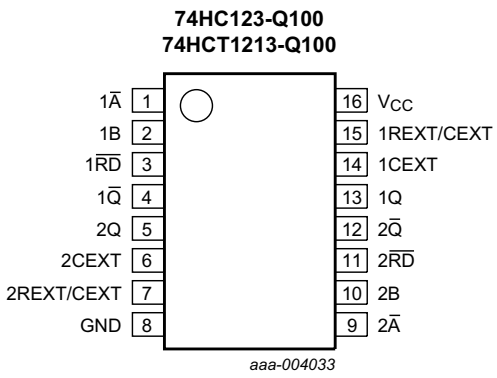
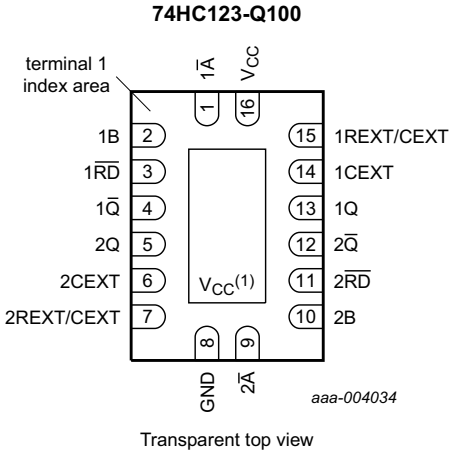


Fig 5. Pin configuration for SO16 and TSSOP16



(1) The die substrate is attached to this pad using conductive die attach material. It cannot be used as supply pin or input.

Fig 6. Pin configuration for DHVQFN16

5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1$\overline{A}$	1	negative-edge triggered input 1
1B	2	positive-edge triggered input 1
1$\overline{RD}$	3	direct reset LOW and positive-edge triggered input 1
1$\overline{Q}$	4	active LOW output 1
2Q	5	active HIGH output 2
2CEXT	6	external capacitor connection 2
2REXT/CEXT	7	external resistor and capacitor connection 2
GND	8	ground (0 V)
2$\overline{A}$	9	negative-edge triggered input 2
2B	10	positive-edge triggered input 2
2$\overline{RD}$	11	direct reset LOW and positive-edge triggered input 2
2$\overline{Q}$	12	active LOW output 2
1Q	13	active HIGH output 1
1CEXT	14	external capacitor connection 1
1REXT/CEXT	15	external resistor and capacitor connection 1
V_{CC}	16	supply voltage

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6. Functional description

Table 3. Function table[1]

Input			Output	
nRD	**nA**	**nB**	**nQ**	**nQ**
L	X	X	L	H
X	H	X	L[2]	H[2]
X	X	L	L[2]	H[2]
H	L	↑	⎍	⎍
H	↓	H	⎍	⎍
↑	L	H	⎍	⎍

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; ↑ = LOW-to-HIGH transition; ↓ = HIGH-to-LOW transition; ⎍ = one HIGH level output pulse; ⎍ = one LOW level output pulse.

[2] If the monostable was triggered before this condition was established, the pulse continues as programmed.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			–0.5	+7	V
I_{IK}	input clamping current	$V_I < -0.5$ V or $V_I > V_{CC} + 0.5$ V		-	±20	mA
I_{OK}	output clamping current	$V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V		-	±20	mA
I_O	output current	except for pins nREXT/CEXT; $V_O = -0.5$ V to ($V_{CC} + 0.5$ V)		-	±25	mA
I_{CC}	supply current			-	50	mA
I_{GND}	ground current			-	–50	mA
T_{stg}	storage temperature			–65	+150	°C
P_{tot}	total power dissipation					
	SO16 package		[3]	-	500	mW
	TSSOP16 package		[4]	-	500	mW
	DHVQFN16 package		[5]	-	500	mW

[3] For SO16 packages: P_{tot} derates linearly with 8 mW/K above 70 °C.

[4] For TSSOP16 packages: P_{tot} derates linearly with 5.5 mW/K above 60 °C.

[5] For DHVQFN16 packages: P_{tot} derates linearly with 4.5 mW/K above 60 °C.

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8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	74HC123-Q100			74HCT123-Q100			Unit
			Min	Typ	Max	Min	Typ	Max	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V_I	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
$\Delta t/\Delta V$	input transition rise and fall rate	$n\overline{RD}$ input							
		V_{CC} = 2.0 V	-	-	625	-	-	-	ns/V
		V_{CC} = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		V_{CC} = 6.0 V	-	-	83	-	-	-	ns/V
T_{amb}	ambient temperature		–40	+25	+125	–40	+25	+125	°C

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC123-Q100										
V_{IH}	HIGH-level input voltage	V_{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
		V_{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V_{CC} = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
		V_{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V_{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}								
		I_O = –20 μA; V_{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I_O = –20 μA; V_{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I_O = –20 μA; V_{CC} = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I_O = –4 mA; V_{CC} = 4.5 V	3.98	4.32	-	3.84	-	3.7	-	V
		I_O = –5.2 mA; V_{CC} = 6.0 V	5.48	5.81	-	5.34	-	5.2	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}								
		I_O = 20 μA; V_{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 20 μA; V_{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 20 μA; V_{CC} = 6.0 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 4 mA; V_{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
		I_O = 5.2 mA; V_{CC} = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
I_I	input leakage current	$V_I = V_{CC}$ or GND; V_{CC} = 6.0 V	-	-	±0.1	-	±1.0	-	±1.0	μA
I_{CC}	supply current	$V_I = V_{CC}$ or GND; I_O = 0 A; V_{CC} = 6.0 V	-	-	8.0	-	80	-	160	μA

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Table 6. Static characteristics *…continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
C_I	input capacitance		-	3.5	-	-	-	-	-	pF
74HCT123-Q100										
V_{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}; V_{CC} = 4.5 V								
		I_O = –20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I_O = –4 mA	3.98	4.32	-	3.84	-	3.7	-	V
V_{OL}	LOW-level output voltage	V_I = V_{IH} or V_{IL}; V_{CC} = 4.5 V								
		I_O = 20 μA	-	0	0.1	-	0.1	-	0.1	V
		I_O = 4.0 mA	-	0.15	0.26	-	0.33	-	0.4	V
I_I	input leakage current	V_I = V_{CC} or GND; V_{CC} = 5.5 V	-	-	±0.1	-	±1.0	-	±1.0	μA
I_{CC}	supply current	V_I = V_{CC} or GND; I_O = 0 A; V_{CC} = 5.5 V	-	-	8.0	-	80	-	160	μA
ΔI_{CC}	additional supply current	per input pin; I_O = 0 A; V_I = V_{CC} − 2.1 V; other inputs at V_{CC} or GND; V_{CC} = 4.5 V to 5.5 V								
		pins $n\overline{A}$, nB	-	35	125	-	160	-	170	μA
		pin $n\overline{RD}$	-	50	180	-	225	-	245	μA
C_I	input capacitance		-	3.5	-	-	-	-	-	pF

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10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); C_L = 50 pF unless otherwise specified; for test circuit see Figure 12.

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC123-Q100										
t_{pd}	propagation delay	$n\overline{RD}$, nA, nB to nQ or $n\overline{Q}$; C_{EXT} = 0 pF; R_{EXT} = 5 kΩ; see Figure 9 [1]								
		V_{CC} = 2.0 V	-	83	255	-	320	-	385	ns
		V_{CC} = 4.5 V	-	30	51	-	64	-	77	ns
		V_{CC} = 5 V; C_L = 15 pF	-	26	-	-	-	-	-	ns
		V_{CC} = 6.0 V	-	24	43	-	54	-	65	ns
		$n\overline{RD}$ (reset) to nQ or $n\overline{Q}$; C_{EXT} = 0 pF; R_{EXT} = 5 kΩ; see Figure 9								
		V_{CC} = 2.0 V	-	66	215	-	270	-	325	ns
		V_{CC} = 4.5 V	-	24	43	-	54	-	65	ns
		V_{CC} = 5 V; C_L = 15 pF	-	20	-	-	-	-	-	ns
		V_{CC} = 6.0 V	-	19	37	-	46	-	55	ns
t_t	transition time	see Figure 9 [1]								
		V_{CC} = 2.0 V	-	19	75	-	95	-	110	ns
		V_{CC} = 4.5 V	-	7	15	-	19	-	22	ns
		V_{CC} = 6.0 V	-	6	13	-	16	-	19	ns
t_W	pulse width	$n\overline{A}$ LOW; see Figure 10								
		V_{CC} = 2.0 V	100	8	-	125	-	150	-	ns
		V_{CC} = 4.5 V	20	3	-	25	-	30	-	ns
		V_{CC} = 6.0 V	17	2	-	21	-	26	-	ns
		nB HIGH; see Figure 10								
		V_{CC} = 2.0 V	100	17	-	125	-	150	-	ns
		V_{CC} = 4.5 V	20	6	-	25	-	30	-	ns
		V_{CC} = 6.0 V	17	5	-	21	-	26	-	ns
		$n\overline{RD}$ LOW; see Figure 11								
		V_{CC} = 2.0 V	100	14	-	125	-	150	-	ns
		V_{CC} = 4.5 V	20	5	-	25	-	30	-	ns
		V_{CC} = 6.0 V	17	4	-	21	-	26	-	ns
		nQ HIGH and $n\overline{Q}$ LOW; V_{CC} = 5.0 V; see Figure 10 and Figure 11 [2]								
		C_{EXT} = 100 nF; R_{EXT} = 10 kΩ	-	450	-	-	-	-	-	µs
		C_{EXT} = 0 pF; R_{EXT} = 5 kΩ	-	75	-	-	-	-	-	ns

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Table 7. Dynamic characteristics *...continued*

Voltages are referenced to GND (ground = 0 V); C_L = 50 pF unless otherwise specified; for test circuit see Figure 12.

Symbol	Parameter	Conditions		25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
t_{rtrig}	retrigger time	$n\overline{A}$, nB; C_{EXT} = 0 pF; R_{EXT} = 5 kΩ; V_{CC} = 5.0 V; see Figure 10	[3][4]	-	110	-	-	-	-	-	ns
R_{EXT}	external resistance	see Figure 7									
		V_{CC} = 2.0 V		10	-	1000	-	-	-	-	kΩ
		V_{CC} = 5.0 V		2	-	1000	-	-	-	-	kΩ
C_{EXT}	external capacitance	V_{CC} = 5.0 V; see Figure 7	[4]	-	-	-	-	-	-	-	pF
C_{PD}	power dissipation capacitance	per monostable; V_I = GND to V_{CC}	[5]	-	54	-	-	-	-	-	pF
74HCT123-Q100											
t_{PHL}	HIGH to LOW propagation delay	$n\overline{RD}$, $n\overline{A}$, nB to nQ or $n\overline{Q}$; C_{EXT} = 0 pF; R_{EXT} = 5 kΩ; see Figure 9									
		V_{CC} = 4.5 V		-	30	51	-	64	-	77	ns
		V_{CC} = 5 V; C_L = 15 pF		-	26	-	-	-	-	-	ns
		$n\overline{RD}$ (reset) to nQ or $n\overline{Q}$; C_{EXT} = 0 pF; R_{EXT} = 5 kΩ; see Figure 9									
		V_{CC} = 4.5 V		-	27	46	-	58	-	69	ns
		V_{CC} = 5 V; C_L = 15 pF		-	23	-	-	-	-	-	ns
t_{PLH}	LOW to HIGH propagation delay	$n\overline{RD}$, $n\overline{A}$, nB to nQ or $n\overline{Q}$; C_{EXT} = 0 pF; R_{EXT} = 5 kΩ; see Figure 9									
		V_{CC} = 4.5 V		-	28	51	-	64	-	77	ns
		V_{CC} = 5 V; C_L = 15 pF		-	26	-	-	-	-	-	ns
		$n\overline{RD}$ (reset) to nQ or $n\overline{Q}$; C_{EXT} = 0 pF; R_{EXT} = 5 kΩ; see Figure 9									
		V_{CC} = 4.5 V		-	23	46	-	58	-	69	ns
		V_{CC} = 5 V; C_L = 15 pF		-	23	-	-	-	-	-	ns
t_t	transition time	V_{CC} = 4.5 V; see Figure 9	[1]	-	7	15	-	19	-	22	ns
t_W	pulse width	V_{CC} = 4.5 V									
		$n\overline{A}$ LOW; see Figure 10		20	3	-	25	-	30	-	ns
		nB HIGH; see Figure 10		20	5	-	25	-	30	-	ns
		$n\overline{RD}$ LOW; see Figure 11		20	7	-	25	-	30	-	ns
		nQ HIGH and $n\overline{Q}$ LOW; V_{CC} = 5.0 V; see Figure 10 and Figure 11	[2]								
		C_{EXT} = 100 nF; R_{EXT} = 10 kΩ		-	450	-	-	-	-	-	µs
		C_{EXT} = 0 pF; R_{EXT} = 5 kΩ		-	75	-	-	-	-	-	ns

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Table 7. Dynamic characteristics *...continued*

Voltages are referenced to GND (ground = 0 V); C_L = 50 pF unless otherwise specified; for test circuit see Figure 12.

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t_{rtrig}	retrigger time	$\overline{nA}$, nB; C_{EXT} = 0 pF; R_{EXT} = 5 kΩ; V_{CC} = 5.0 V; see Figure 10 [3][4]	-	110	-	-	-	-	-	ns
R_{EXT}	external timing resistor	V_{CC} = 5.0 V; see Figure 7	2	-	1000	-	-	-	-	kΩ
C_{EXT}	external timing capacitor	V_{CC} = 5.0 V; see Figure 7 [4]	-	-	-	-	-	-	-	pF
C_{PD}	power dissipation capacitance	per monostable; V_I = GND to V_{CC} [5]	-	56	-	-	-	-	-	pF

[1] t_{pd} is the same as t_{PHL} and t_{PLH}; t_t is the same as t_{THL} and t_{TLH}

[2] For other R_{EXT} and C_{EXT} combinations, see Figure 7. If C_{EXT} > 10 nF, the following formula is valid.

$t_W = K \times R_{EXT} \times C_{EXT}$, where:

t_W = typical output pulse width in ns;

R_{EXT} = external resistor in kΩ;

C_{EXT} = external capacitor in pF;

K = constant = 0.45 for V_{CC} = 5.0 V and 0.55 for V_{CC} = 2.0 V.

The inherent test jig and pin capacitance at pins 15 and 7 (nREXT/CEXT) is approximately 7 pF.

[3] The time to retrigger the monostable multivibrator depends on the values of R_{EXT} and C_{EXT}. The output pulse width is only extended when the time between the active-going edges of the trigger input pulses meets the minimum retrigger time. If C_{EXT} >10 pF, the next formula (at V_{CC} = 5.0 V) for the setup time of a retrigger pulse is valid:

$t_{rtrig} = 30 + 0.19 \times R_{EXT} \times C_{EXT}^{0.9} + 13 \times R_{EXT}^{1.05}$, where:

t_{rtrig} = retrigger time in ns;

C_{EXT} = external capacitor in pF; R_{EXT} = external resistor in kΩ.

The inherent test jig and pin capacitance at pins 15 and 7 (nREXT/CEXT) is 7 pF.

[4] When the device is powered-up, initiate the device via a reset pulse, when C_{EXT} < 50 pF.

[5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i + \Sigma(C_L \times V_{CC}^2 \times f_o) + 0.75 \times C_{EXT} \times V_{CC}^2 \times f_o + D \times 16 \times V_{CC}$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

D = duty factor in %;

C_L = output load capacitance in pF;

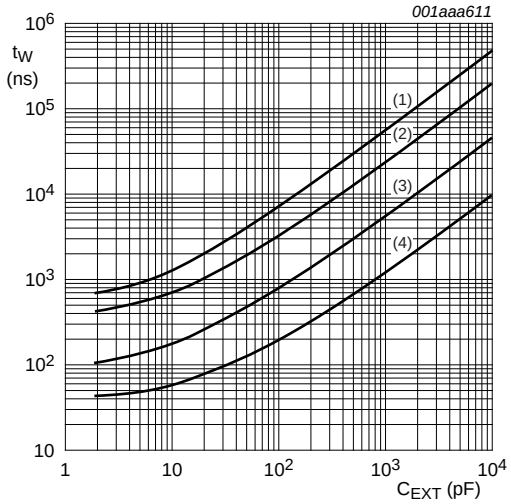
V_{CC} = supply voltage in V;

C_{EXT} = timing capacitance in pF;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ sum of outputs.

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V_{CC} = 5.0 V; T_{amb} = 25 °C.

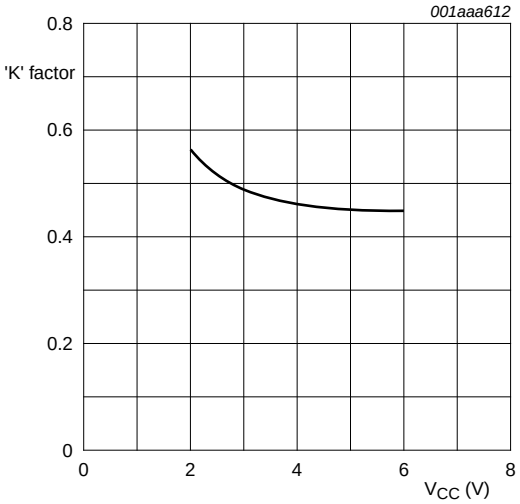
(1) R_{EXT} = 100 kΩ

(2) R_{EXT} = 50 kΩ

(3) R_{EXT} = 10 kΩ

(4) R_{EXT} = 2 kΩ

Fig 7. Typical output pulse width as a function of the external capacitor value



C_{EXT} = 10 nF; R_{EXT} = 10 kΩ to 100 kΩ.

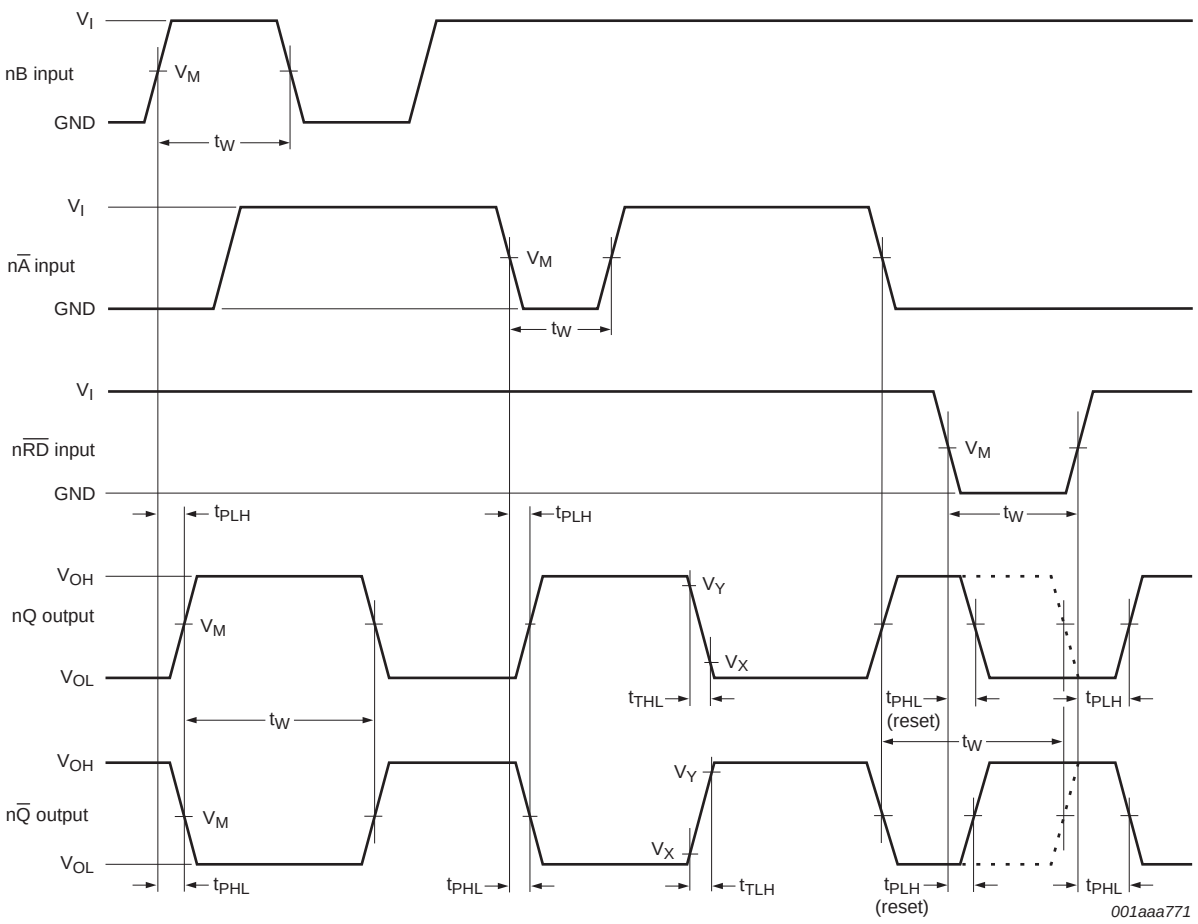
T_{amb} = 25 °C.

Fig 8. 74HC123-Q100 typical 'K' factor as function of V_{CC}

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11. Waveforms



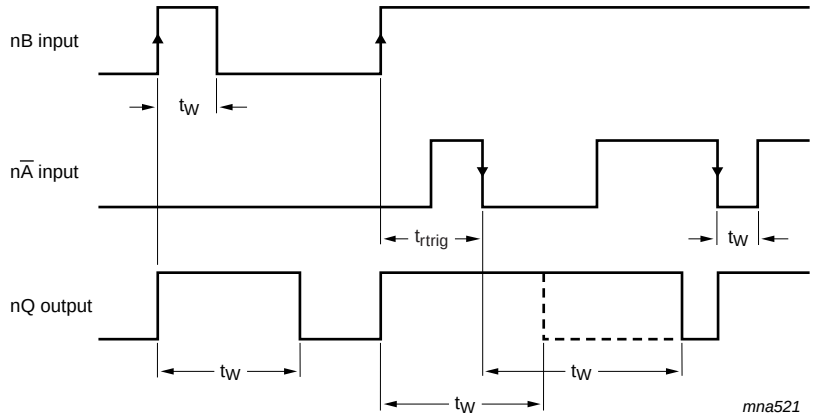
Measurement points are given in Table 8.

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 9. Propagation delays from inputs ($\overline{nA}$, nB, $\overline{nRD}$) to outputs (nQ, $\overline{nQ}$) and output transition times

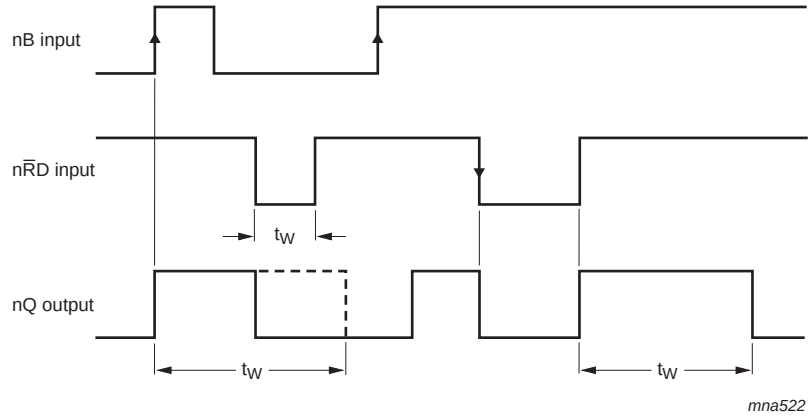
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$n\overline{RD}$ = HIGH

Fig 10. Output pulse control using retrigger pulse

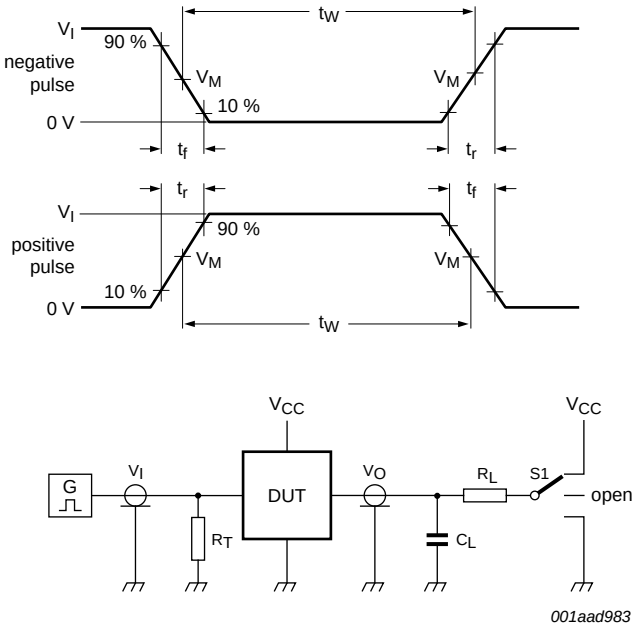


$n\overline{A}$ = LOW

Fig 11. Output pulse control using reset input $n\overline{RD}$

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Test data is given in Table 8.

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = Load capacitance including jig and probe capacitance.

R_L = Load resistance.

S1 = Test selection switch.

Fig 12. Test circuit for measuring switching times

Table 8. Test data

Type	Input		Load		S1 position
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}
74HC123-Q100	V_{CC}	6 ns	15 pF, 50 pF	1 kΩ	open
74HCT123-Q100	3 V	6 ns	15 pF, 50 pF	1 kΩ	open

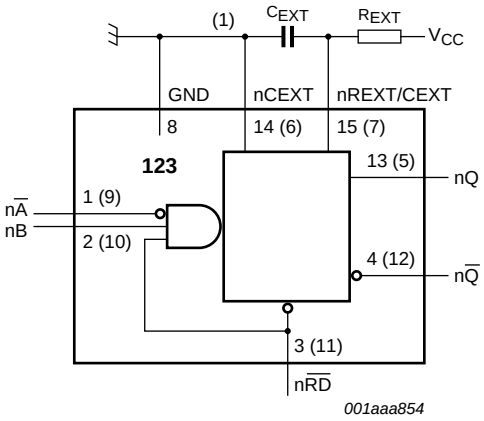
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12. Application information

12.1 Timing component connections

The basic output pulse width is defined by the values of the external timing components R_{EXT} and C_{EXT}.



(1) For minimum noise generation, ground pins 6 (2CEXT) and 14 (1CEXT) externally to pin 8 (GND).

Fig 13. Timing component connections

12.2 Power-up considerations

When the monostable is powered-up, it may produce an output pulse, with a pulse width defined by the values of R_{EXT} and C_{EXT}. This output pulse can be eliminated using the circuit shown in Figure 14.

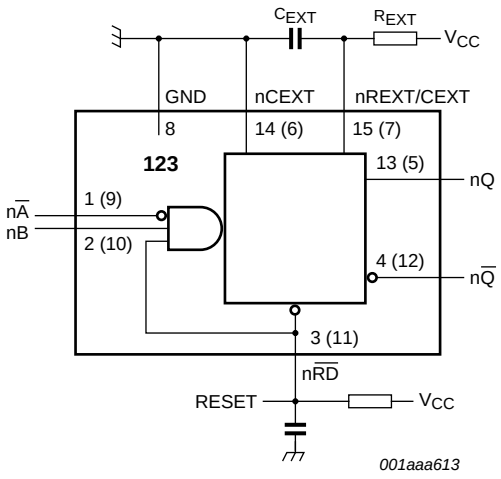


Fig 14. Power-up output pulse elimination circuit

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12.3 Power-down considerations

A large capacitor C_{EXT} may cause problems when powering-down the monostable due to the energy stored in this capacitor. When a system containing this device is powered-down or a rapid decrease of V_{CC} to zero occurs, the monostable may sustain damage. The damage is due to the capacitor discharging through the input protection diodes. To avoid this possibility, use a damping diode (D_{EXT}) and connect as shown in Figure 15. D_{EXT} is preferably a germanium or Schottky type diode able to withstand large current surges.

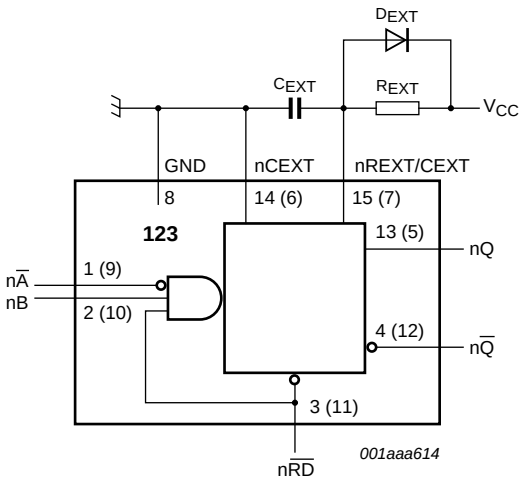


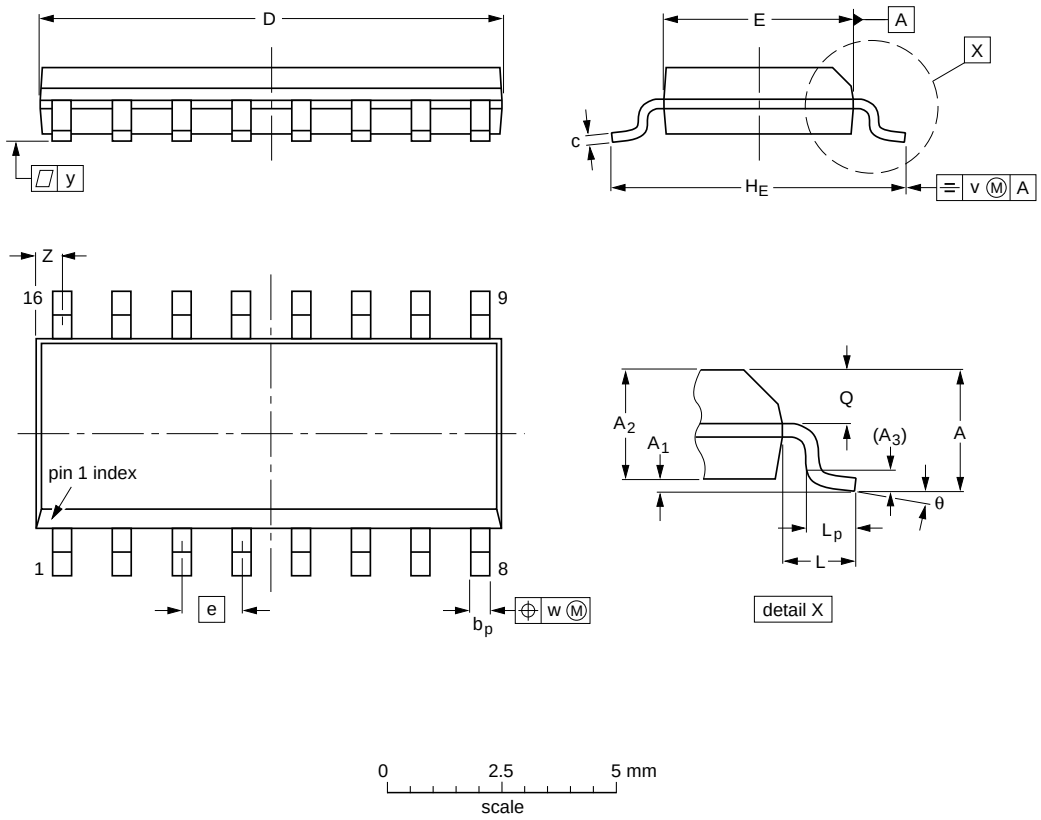
Fig 15. Power-down protection circuit

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13. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm **SOT109-1**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	10.0 9.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8^o 0^o
inches	0.069	0.010 0.004	0.057 0.049	0.01	0.019 0.014	0.0100 0.0075	0.39 0.38	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.020	0.01	0.01	0.004	0.028 0.012	

Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

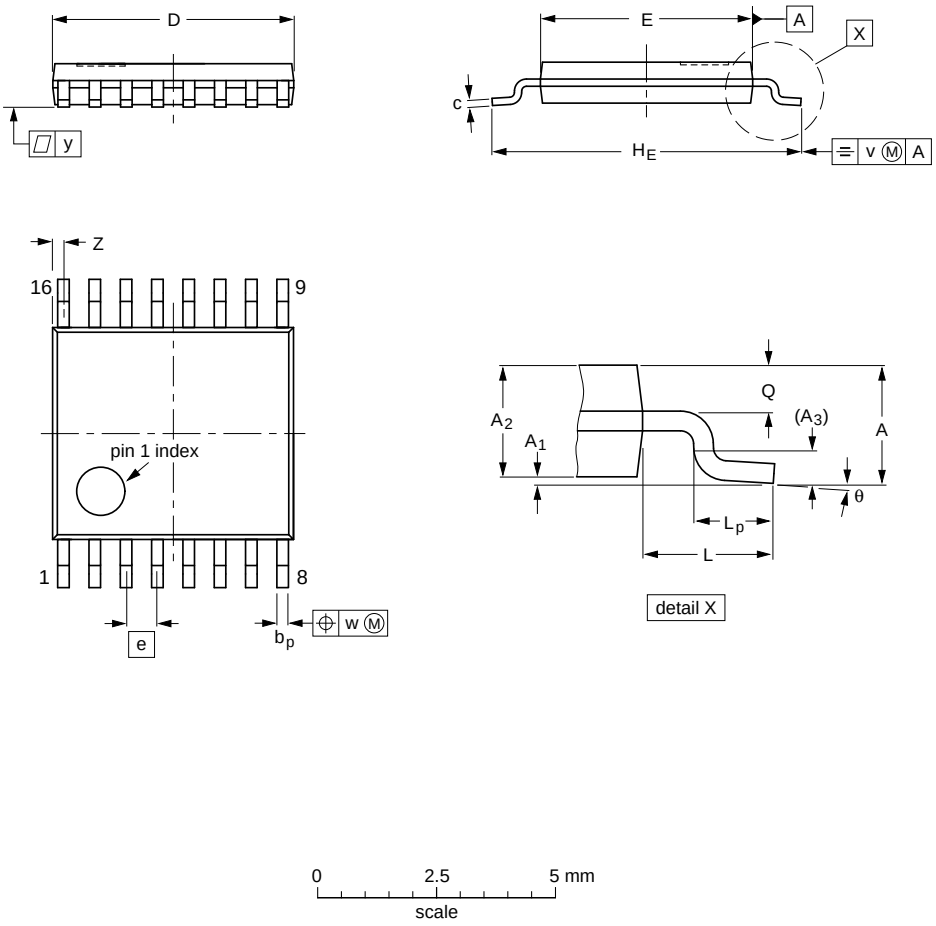
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT109-1	076E07	MS-012				~~99-12-27~~ 03-02-19

Fig 16. Package outline SOT109-1 (SO16)

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TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm **SOT403-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (2)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.40 0.06	8^o 0^o

Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

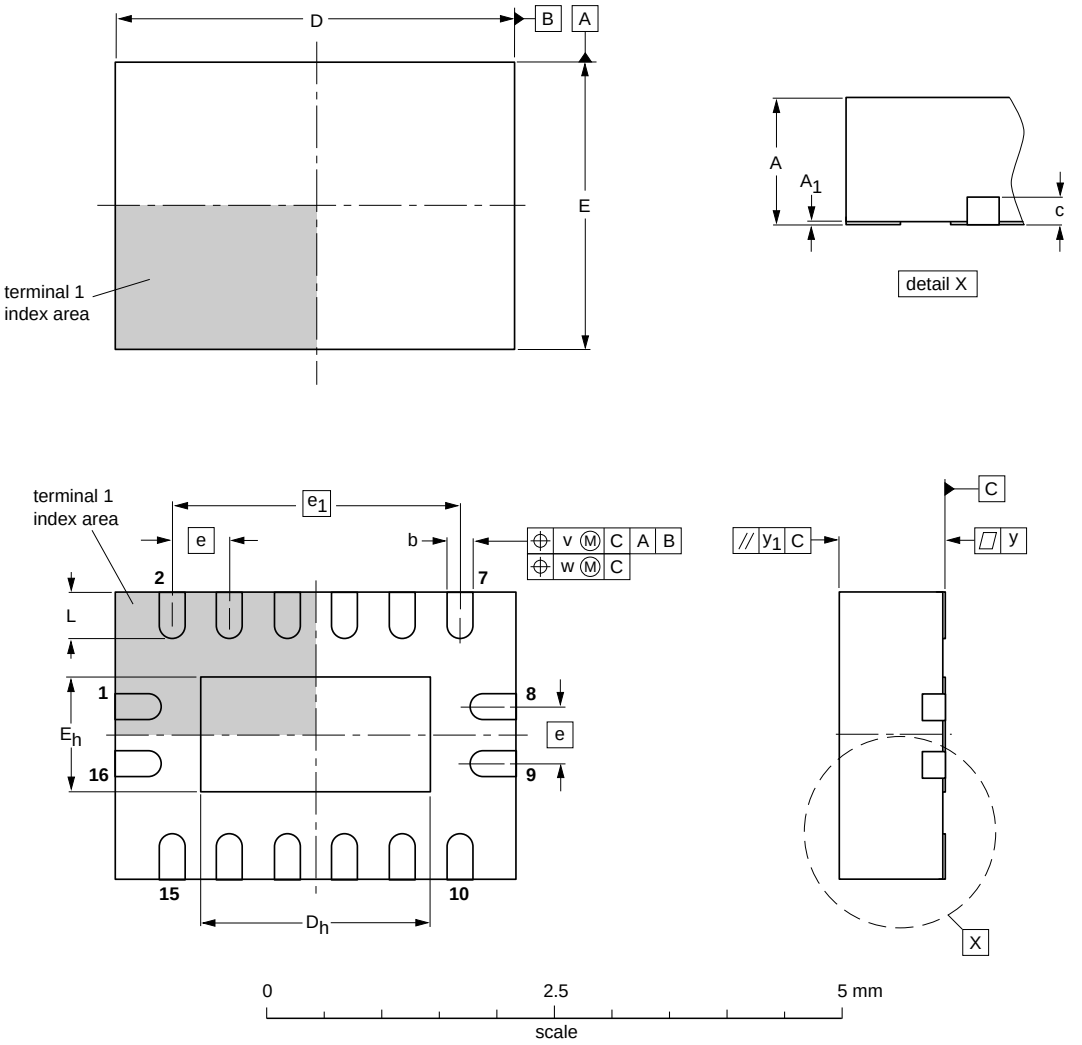
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT403-1		MO-153				~~99-12-27~~ 03-02-18

Fig 17. Package outline SOT403-1 (TSSOP16)

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DHVQFN16: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 x 3.5 x 0.85 mm **SOT763-1**



DIMENSIONS (mm are the original dimensions)

UNIT	$A^{(1)}$ max.	A_1	b	c	$D^{(1)}$	D_h	$E^{(1)}$	E_h	e	e_1	L	v	w	y	y_1
mm	1	0.05 0.00	0.30 0.18	0.2	3.6 3.4	2.15 1.85	2.6 2.4	1.15 0.85	0.5	2.5	0.5 0.3	0.1	0.05	0.05	0.1

Note

1. Plastic or metal protrusions of 0.075 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
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SOT763-1	- - -	MO-241	- - -			~~02-10-17~~ 03-01-27

Fig 18. Package outline SOT763-1 (DHVQFN16)

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14. Abbreviations

Table 9. Abbreviations

Acronym	Abbreviation
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
LSTTL	Low-power Schottky Transistor-Transistor Logic
MM	Machine Model
MIL	Military

15. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT123_Q100 v.1	20120801	Product data sheet	-	-

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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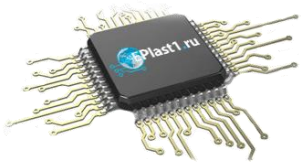
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